

# Bulk superconductivity in $\text{Bi}_4\text{O}_4\text{S}_3$ revealed by specific heat measurement

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Since the recent discovery of superconductivity in  $\text{Bi}_4\text{O}_4\text{S}_3$ , the  $\text{BiS}_2$ -based superconducting family has attracted many researchers<sup>1–11</sup> because of some analogies to cuprates and Fe-based superconductors.<sup>12–14</sup> The parent phase of the  $\text{Bi}_4\text{O}_4\text{S}_3$  superconductor is  $\text{Bi}_6\text{O}_8\text{S}_5$  with a crystal structure composed of a stacking of  $\text{Bi}_2\text{S}_4$  layers (two  $\text{BiS}_2$  layers) and  $\text{Bi}_4\text{O}_4(\text{SO}_4)$  spacer layers.<sup>1</sup> Band calculations<sup>1,9</sup> indicate that  $\text{Bi}_6\text{O}_8\text{S}_5$  is an insulator with  $\text{Bi}^{3+}$ . Superconducting  $\text{Bi}_4\text{O}_4\text{S}_3$  is expected to possess 50% defects at a  $\text{SO}_4$  site, which generates electron carriers within the  $\text{BiS}_2$  layers. In fact, superconductivity of  $\text{Bi}_4\text{O}_4\text{S}_3$  is induced by electron doping into the  $\text{BiS}_2$  layers via the defects of the  $\text{SO}_4$  ions at the interlayer site.<sup>1</sup> To date,  $\text{LaOBiS}_2$  and  $\text{NdOBiS}_2$ , having analogous  $\text{BiS}_2$  layers, have been found to show superconductivity by electron doping as well.<sup>2,3</sup> Although the nature of superconductivity in the  $\text{BiS}_2$  family has not been clarified so far, the relatively high transition temperature ( $T_c$ ), for example, 10.6 K in  $\text{La}(\text{O},\text{F})\text{BiS}_2$ , attracts researchers to exploring new  $\text{BiS}_2$ -based superconductors with a higher  $T_c$ . To elucidate the superconductivity mechanism or design new  $\text{BiS}_2$ -based superconductors, it is important to clarify whether the observed superconductivity is bulk or occurred in surface. Here we show the evidence of bulk superconductivity in  $\text{Bi}_4\text{O}_4\text{S}_3$  revealed by the specific heat measurements.

The polycrystalline  $\text{Bi}_4\text{O}_4\text{S}_3$  sample was prepared by the conventional solid-state reaction method as described in Ref. 1. The sample quality was confirmed by the x-ray diffraction and dc susceptibility measurements. It was comparable to the result reported in Ref. 1. The  $T_c$  was estimated to be  $\sim 4.7$  K. Specific heat was measured with a thermal relaxation method with a commercial calorimeter (PPMS, Quantum Design) down to 2 K.

Figure 1 shows the temperature dependence of the total specific heat  $C_P$  in the superconducting state ( $\mu_0 H = 0$  T) and in the normal-conducting state ( $\mu_0 H = 9$  T  $> \mu_0 H_c$ ). The  $C_P$  anomaly associated with the superconducting transition is observed, as indicated by the arrow ( $T \simeq 4.7$  K). This result ensures that  $\text{Bi}_4\text{O}_4\text{S}_3$  is a bulk superconductor. The tiny jump is attributed to the small electronic-specific-heat coefficient  $\gamma$ . Assuming the BCS weak coupling approximation,  $\Delta C_P / \gamma T_c = 1.43$  and 100% superconducting volume, the  $\gamma$  value was yielded

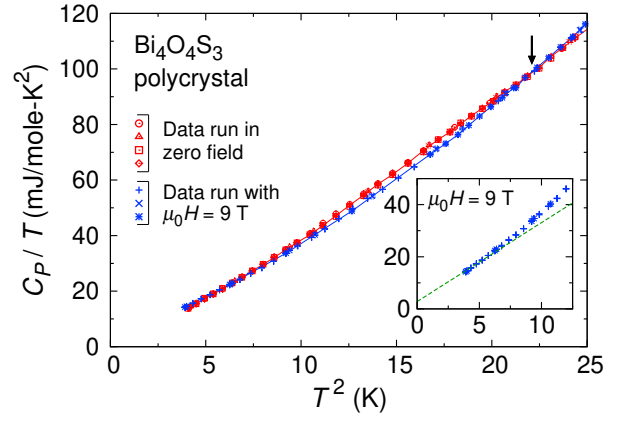


Fig. 1. Temperature dependence of total specific heat  $C_P$  of a polycrystalline sample of  $\text{Bi}_4\text{O}_4\text{S}_3$ . The inset shows the same  $C_P/T$  versus  $T^2$  plot in the low- $T$  region at 9 T (normal state).

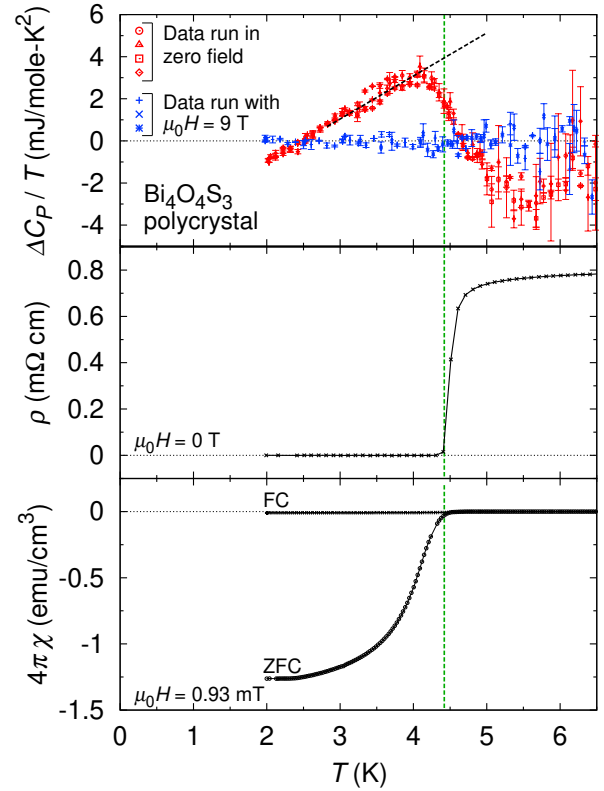


Fig. 2. Temperature dependence of (a) the difference in the electronic specific heat between the superconducting state and the normal-conducting state,  $\Delta C_P = C_P(0\text{T}) - C_P(9\text{T})$ , (b) resistivity  $\rho$ , and (c) dc magnetic susceptibility  $\chi$ . The lines in (a) are entropy-conserving constructions in order to estimate the intrinsic jump height of  $\Delta C_P$ . The transition temperature estimated by  $C_P$  is consistent with that from  $\rho$  and  $\chi$ .

to be about  $2.8 \text{ mJ}/(\text{f.u. mol K}^2)$ . The inset of Fig. 1 presents the fitting result by a conventional relation,  $C_P/T = \gamma + \beta T^2$ , with the estimated  $\gamma$  and the coefficient of the phononic contribution  $\beta$ . Although lower- $T$  data need to evaluate the certain  $\gamma$  value, the data is fairly fitted by the relation with  $\beta = 3.0 \text{ mJ}/(\text{f.u. mol K}^4)$  yielding the Debye temperature  $\Theta_D = 192$  K. We expect that the small  $\gamma$  and low carrier<sup>4</sup> are essential

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for the superconducting mechanism of the BiS<sub>2</sub>-based superconductor.

From the intrinsic jump of  $C_P$ , we define the transition temperature  $T_c = 4.4$  K in zero field, which agrees well with the temperature of the zero-resistivity and the starting temperature of the bifurcation between  $\chi_{FC}$  and  $\chi_{ZFC}$ . In Fig. 2, comparisons between those results are presented. For the  $C_P$  data, the difference in the electronic specific heat between the superconducting and normal-conducting states is estimated by a relation of  $\Delta C_P = C_P(0T) - C_P(9T)$ , since the phononic contribution in  $C_P$  is usually  $H$  independent. We have fitted the 9 T data to a polynomial, and used it in calculating  $\Delta C_P$ . We obtained the intrinsic jump height at  $T_c$  as  $\Delta C_P/T_c = 4.0$  mJ/(f.u. mol K<sup>2</sup>). We note that there is a small discrepancy between  $C_P$  data of the superconducting and normal-conducting states above  $T_c$ . However, this is only 2% of the total specific heat. Therefore, we think that this is not intrinsic in the nature of Bi<sub>4</sub>O<sub>4</sub>S<sub>3</sub>, instead it is attributable to a small error of measurements or of the subtraction of the normal state contribution, because of the small specific heat jump.

In conclusion, our specific heat experiments on a polycrystalline sample of the BiS<sub>2</sub>-based superconductor Bi<sub>4</sub>O<sub>4</sub>S<sub>3</sub> demonstrate that the superconductivity of it is bulk in nature. The  $T_c$  is estimated by the specific heat measurements to be  $T_c = 4.4$  K, consistent with that of the resistivity and dc susceptibility. In order to further discuss the superconductivity mechanism of Bi<sub>4</sub>O<sub>4</sub>S<sub>3</sub>, lower temperature specific heat experiments below 2 K is essential.

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